TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

# TC7SH86F, TC7SH86FU

### **EXCLUSIVE OR GATE**

The TC7SH86 is an advanced high speed CMOS EXCLUSIVE OR GATE fabricated with silicon gate CMOS technology.

It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

The internal circuit is includes on output buffer, which provide high noise immunity and stable output. An input protection circuit ensures that 0V to 7V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5V to 3V system and two supply system such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

### **FEATURES**

- High Speed ...... t<sub>pd</sub> = 4.8ns (Typ.) at V<sub>CC</sub> = 5V
- Low Power Dissipation  $\cdots$   $I_{CC} = 2\mu A$  (Max.) at  $Ta = 25^{\circ}C$
- High Noise Immunity ······· V<sub>NIH</sub> = V<sub>NIL</sub> = 28% V<sub>CC</sub> (Min.)
- Power Down Protection is provided on all inputs.
- Balanced Propagation Delays ······ t<sub>pLH</sub>=t<sub>pHL</sub>
- Wide Operation Voltage Range ··· V<sub>CC</sub> (opr) = 2V~5.5V

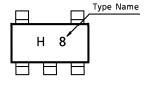
# TC75H86F SSOP5-P-0.95 TC75H86FU SSOP5-P-0.65A

Weight SSOP5-P-0.95 : 0.016g (Typ.) SSOP5-P-0.65A : 0.006g (Typ.)

### **MAXIMUM RATINGS**

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	V <sub>CC</sub>	-0.5~7.0	V
DC Input Voltage	V <sub>IN</sub>	-0.5~7.0	V
DC Output Voltage	Vout	-0.5~V <sub>CC</sub> +0.5	\ \
Input Diode Current	ΙΚ	- 20	mA
Output Diode Current	loк	± 20	mA
DC Output Current	IOUT	± 25	mA
DC V <sub>CC</sub> / Ground Current	lcc	± 50	mA
Power Dissipation	P <sub>D</sub>	200	mW
Storage Temperature	T <sub>stg</sub>	<b>-65∼150</b>	°C
Lead Temperature (10 s)	TL	260	°C

### **MARKING**



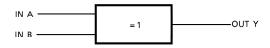
### TRUTH TABLE

Α	В	Υ
L	L	L
L	Н	Н
Н	L	Н
Н	Н	L

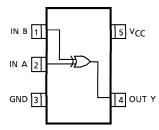
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### **LOGIC DIAGRAM**



# PIN ASSIGNMENT (TOP VIEW)



### **RECOMMENDED OPERATING CONDITIONS**

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Supply Voltage	Vcc	2.0~5.5	V	
Input Voltage	VIN	0~5.5	V	
Output Voltage	VOUT	0~V <sub>CC</sub>	V	
Operating Temperature	T <sub>opr</sub>	- 40~85	°C	
Input Rise and Fall Time	dt / dv	$0 \sim 100 \text{ (V}_{CC} = 3.3 \pm 0.3 \text{V)}$	ns/V	
input Rise and Fall Time	ut/dv	$0\sim20 \ (V_{CC} = 5 \pm 0.5V)$	] 113 / V	

### DC ELECTRICAL CHARACTERISTICS

CHADACTERISTIC	CVAADOL	TEST CONDITION			Ta = 25°C			Ta = −40~85°C		UNIT
CHARACTERISTIC	SYMBOL			VCC	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT
High-Level				2.0	1.50	_		1.50		
Input Voltage	V <sub>IH</sub>			3.0~ 5.5	V <sub>CC</sub> ×0.7	_	_	V <sub>CC</sub> ×0.7	1	V
Low-Level				2.0		_	0.50	_	0.50	
Input Voltage	V <sub>IL</sub>			3.0~ 5.5	1	_	V <sub>C</sub> C ×0.3	_	V <sub>C</sub> C ×0.3	V
	Vон	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OH</sub> = -50μA	2.0	1.9	2.0	_	1.9	_	V
Liab Laval				3.0	2.9	3.0	_	2.9	_	
High-Level Output Voltage				4.5	4.4	4.5	_	4.4	_	
			$I_{OH} = -4mA$	3.0	2.58	_	_	2.48	_	
			$I_{OH} = -8mA$	4.5	3.94	_	_	3.80	_	
	V <sub>OL</sub> =	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>   I <sub>OL</sub> = 50μA   I <sub>OL</sub> = 4mA   I <sub>OL</sub> = 8mA	I <sub>OL</sub> = 50μA	2.0	_	0.0	0.1		0.1	
Low-Level				3.0		0.0	0.1	_	0.1	
Output Voltage			4.5	_	0.0	0.1		0.1	] v	
Output Voltage			$I_{OL} = 4mA$	3.0	_		0.36		0.44	_
			$I_{OL} = 8mA$	4.5		1	0.36	<b>—</b>	0.44	
Input Leakage Current	lIN	V <sub>IN</sub> = 5.5V or GND		0~ 5.5			± 0.1		± 1.0	μΑ
Quiescent Supply Current	lcc	V <sub>IN</sub> = V <sub>CC</sub> or GND		5.5			2.0	_	20.0	μΑ

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 The information contained herein is subject to change without notice.

AC	FLECTRICAL	<b>CHARACTERISTICS</b>	(Input $t_r = t_f = 3ns$ )
$\sim$		CHANACHERISHES	(III) Dut tr — tr — JII3/

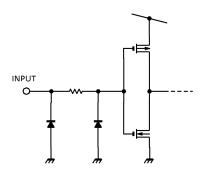
CHARACTERISTIC	SYMBOL TEST	TEST C	ST CONDITION		Ta = 25°C			Ta = −40~85°C		LINUT
			V <sub>CC</sub> (V)	C <sub>L</sub> (pF)	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT
Propagation Delay Time			3.3 ± 0.3	15		7.0	11.0	1.0	13.0	ns
	t <sub>pLH</sub>			50		9.5	14.5	1.0	16.5	
			5.0 ± 0.5	15		4.8	6.8	1.0	8.0	
				50		6.3	8.8	1.0	10.0	
Input Capacitance	C <sub>IN</sub>					4	10	_	10	рF
Power Dissipation	CDD	(NI	(Note 1)			18				рF
Capacitance	C <sub>PD</sub>	(14)				10	l <u></u>			ן א

(Note 1): CpD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

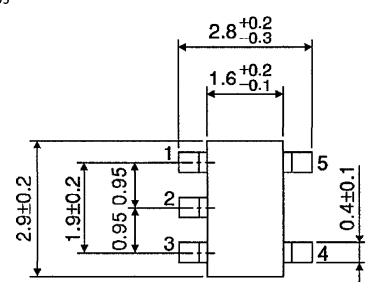
ICC (opr) = CpD · VCC · fIN + ICC

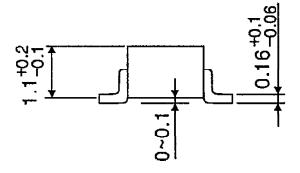
### INPUT EQUIVALENT CIRCUIT



### OUTLINE DRAWING SSOP5-P-0.95

Unit: mm

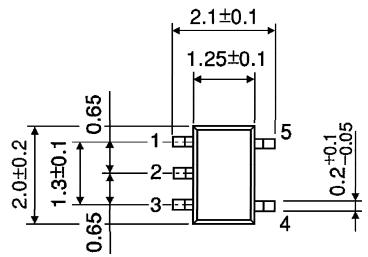




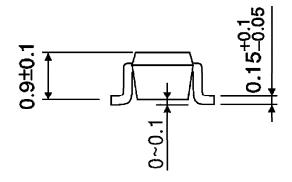
Weight: 0.016g (Typ.)

## **OUTLINE DRAWING**

SSOP5-P-0.65A



Unit: mm



Weight: 0.006g (Typ.)